

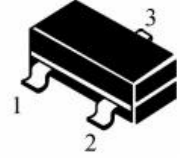


安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

BAS70/-04/-05/-06

SOT-23 Schottky Barrier Diode 肖特基势垒二极管



Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAS70	BAS70-04	BAS70-05	BAS70-06
Pin 管脚				
Mark 打标	73	74	75	76

Absolute Maximum Ratings 最大额定值

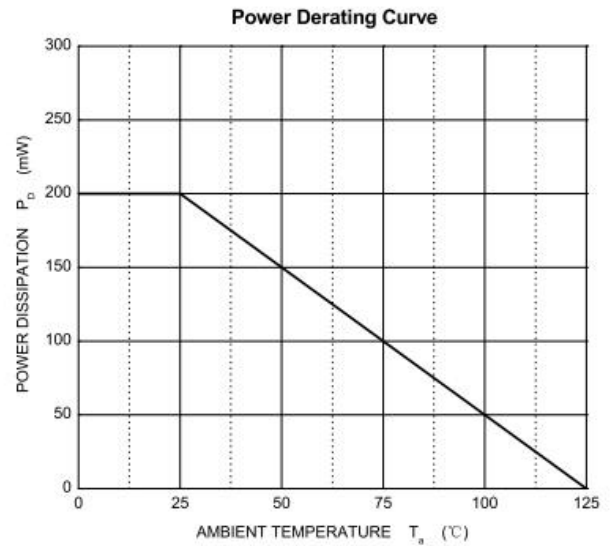
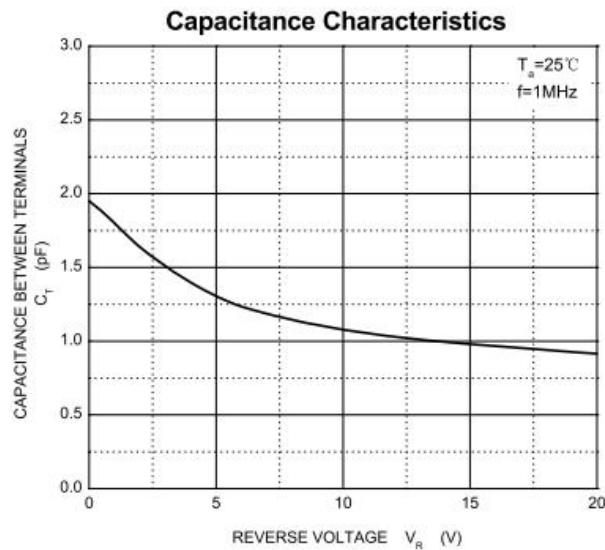
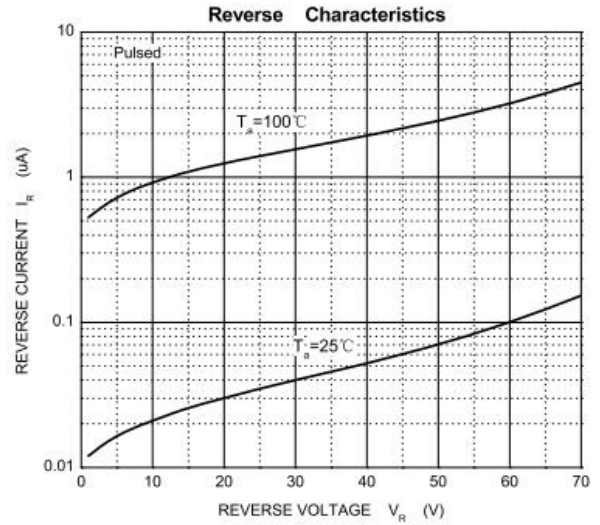
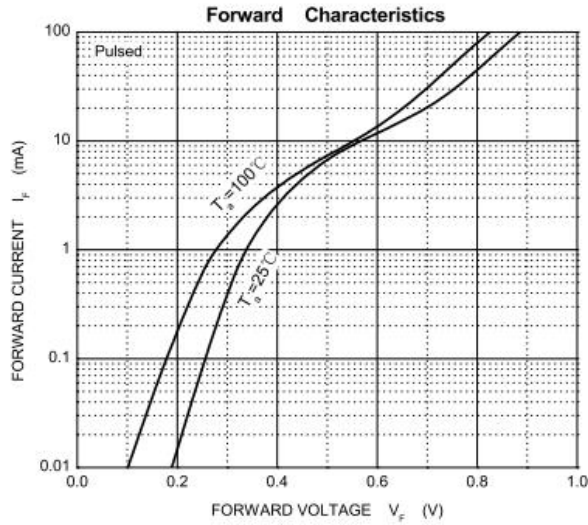
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	70	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	70	mA
Peak Forward Current 正向峰值电流	I_{FM}	100	mA
Power dissipation 耗散功率	$P_D(T_a=25^\circ C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	625	$^\circ C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ C$	

Electrical Characteristics 电特性

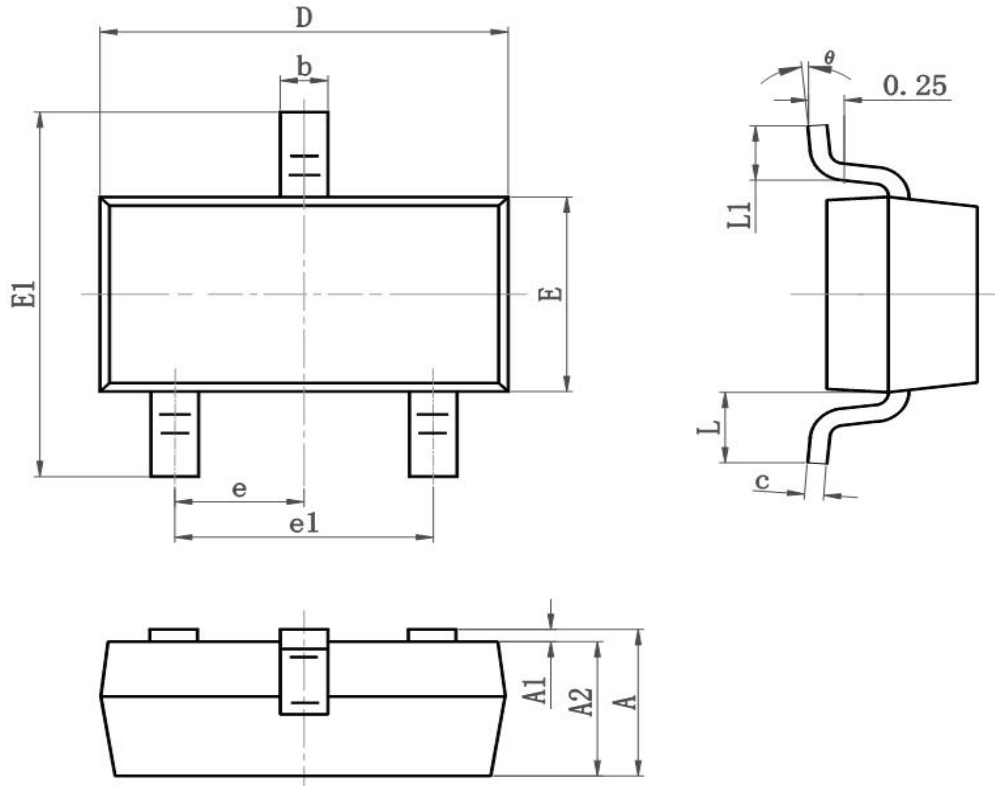
($T_A=25^\circ C$ unless otherwise noted 如无特殊说明, 温度为 $25^\circ C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=10\mu A$)	$V_{(BR)}$	70	—	V
Reverse Leakage Current 反向漏电流($V_R=50V$)	I_R	—	100	nA
Forward Voltage($I_F=1mA$) 正向电压($I_F=10mA$) ($I_F=15mA$)	V_F	—	0.41 0.75 1	V
Diode Capacitance 二极管电容($V_R=0V, f=1MHz$)	C_T	—	2	pF
Reverse Recovery Time 反向恢复时间	T_{rr}	—	5	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.050	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°